

Diode

Silicon Carbide Schottky Diode

IDM05G120C5

5th Generation CoolSiC™ 1200 V SiC Schottky Diode

Final Datasheet

Rev. 2.1 2021-06-09

Industrial Power Control



CoolSiC[™] SiC Schottky Diode

Features:

- Revolutionary semiconductor material Silicon Carbide
- No reverse recovery current / No forward recovery
- Temperature independent switching behavior
- Low forward voltage even at high operating temperature
- Tight forward voltage distribution
- Excellent thermal performance
- Extended surge current capability
- Specified dv/dt ruggedness
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant

Benefits

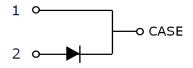
- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI
- Related Links: www.infineon.com/sic

Applications

- Solar inverters
- Uninterruptable power supplies
- Motor drives
- Power Factor Correction

Package pin definitions

- Pin 1 and backside cathode
- Pin 2 anode













Key Performance and Package Parameters

Туре	V _{DC}	I F	Q _C	T _{j,max}	Marking	Package
IDM05G120C5	1200V	5A	24nC	175°C	D0512C5	PG-TO252-2

1) J-STD20 and JESD22





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Maximum ratings

Parameter	Symbol	Value	Unit V	
Repetitive peak reverse voltage	V _{RRM}	1200		
Continoues forward current for $R_{th(j-c,max)}$ $T_C = 164^{\circ}C$, D=1 $T_C = 135^{\circ}C$, D=1 $T_C = 25^{\circ}C$, D=1	l _F	5 10.8 22.2		
Surge non-repetitive forward current, sine halfwave $T_{\rm C}$ =25°C, $t_{\rm p}$ =10ms $T_{\rm C}$ =150°C, $t_{\rm p}$ =10ms	I F,SM	59 50	Α	
Non-repetitive peak forward current $T_C = 25^{\circ}C$, $t_p=10 \mu s$	I _{F,max}	472		
i ² t value $T_C = 25$ °C, t_p =10 ms $T_C = 150$ °C, t_p =10 ms	∫ i²dt	17.4 12.5	A²s	
Diode dv/dt ruggedness V_R =0960 V	d <i>v</i> /d <i>t</i>	150	V/ns	
Power dissipation $T_C = 25$ °C	P _{tot}	144	W	
Operating temperature	T _j	-55175		
Storage temperature	T _{stg}	-55150	00	
Soldering temperature, Wave- and reflowsoldering allowed (reflow MSL1)	T_{sold}	260	°C	

Thermal Resistances

Danamatan	0	O and Italiana	Value			11
Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Characteristic	•					•
Diode thermal resistance, junction – case	R _{th(j-c)}		-	0.8	1.04	
Thermal resistance, junction – ambient	D. a.s.	SMD version, device on PCB, minimal footprint	-	-	62	K/W
	R _{th(j-a)}	SMD version, device on PCB, 6 cm² cooling area²)		35		

²⁾ Device on 40 mm*40mm*1.5 epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper for cathode connection. PCB is vertical without air stream cooling.



Electrical Characteristics

Static Characteristic, at Tj=25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
raiailletei	Symbol		min.	typ.	max.	Oilit
DC blocking voltage	$V_{\rm DC}$	<i>T</i> _j = 25°C	1200	-	-	V
Diode forward voltage	V _F	<i>I</i> _F = 5 A, <i>T</i> _j =25°C	-	1.50	1.8	V
Diode forward voltage		<i>I</i> _F = 5 A, <i>T</i> _j =150°C	-	1.95	2.6	
Reverse current	L	V _R =1200 V, T _j =25°C		2.5	33	
Reverse current	I R	<i>V</i> _R =1200 V, <i>T</i> _j =150°C		12	175	μΑ

Dynamic Characteristics, at T_j=25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
raiailletei	Syllibol		min.	typ.	max.	Offic
Total capacitive charge		$V_{R} = 800 \text{ V}, T_{j} = 150 ^{\circ}\text{C}$				
	Q _C	$Q_C = \int_0^{V_R} C(V) dV$	-	24	-	nC
		V _R =1 V, f=1 MHz	-	301		
Total Capacitance	С	V _R =400 V, <i>f</i> =1 MHz	-	21	-	pF
		V _R =800 V, f=1 MHz	-	17	-	



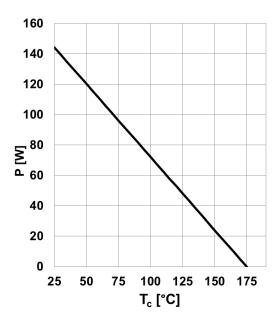


Figure 1. Power dissipation as a function of case temperature, $P_{tot}=f(T_C)$, $R_{th(j-c),max}$

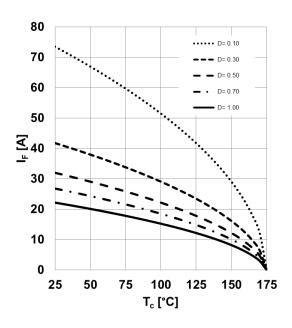


Figure 2. **Diode forward current as function of temperature**, T_j ≤175°C, $R_{\text{th(j-c),max}}$, parameter D=duty cycle, V_{th} , Rdiff @ T_j =175°C

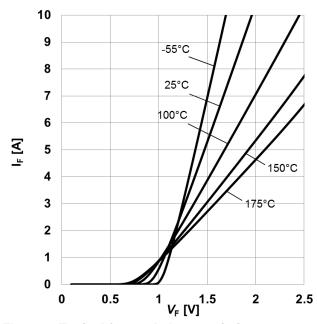


Figure 3. **Typical forward characteristics,** $I_F = f(V_F)$, $t_p = 10 \mu s$, parameter: T_j

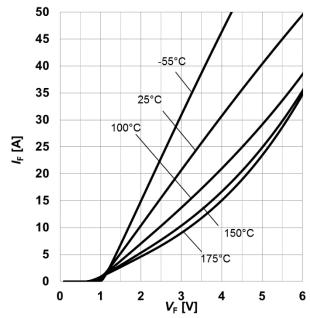


Figure 4. Typical forward characteristics in surge current, $I_F=f(V_F)$, $t_p=10 \mu s$, parameter: T_i



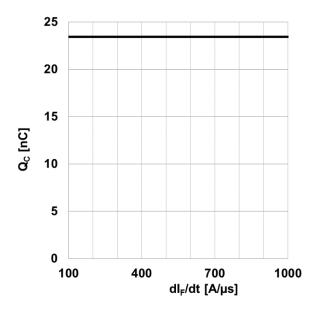


Figure 5. **Typical capacitance charge as function of current slope**¹, $Q_C=f(dI_F/dt)$, $T_j=150$ °C 1) Only capacitive charge, guaranteed by design.

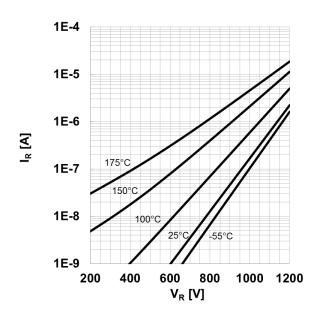


Figure 6. Typical reverse current as function of reverse voltage, $I_R=f(V_R)$, parameter: T_i

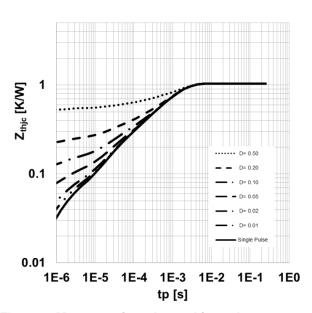


Figure 7. Max. transient thermal impedance, $Z_{\text{th,jc}} = f(t_P)$, parameter: $D = t_P/T$

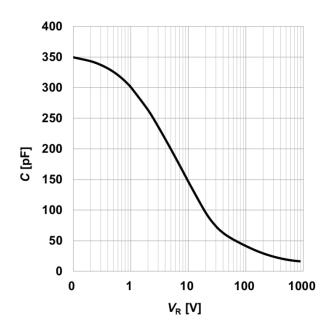


Figure 8. Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_j=25$ °C; f=1 MHz



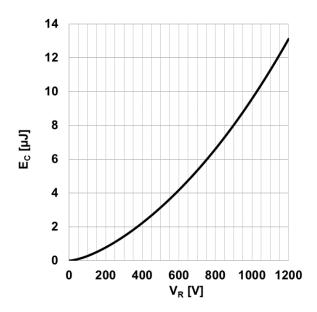
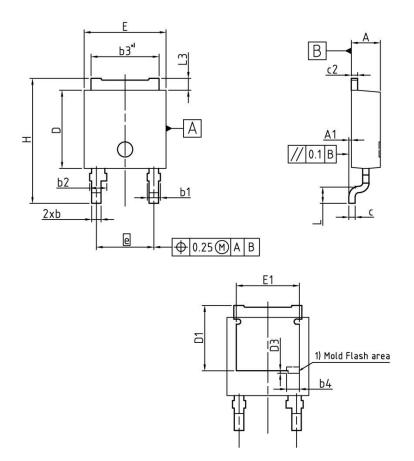


Figure 9. Typical capacitance stored energy as function of reverse voltage,

$$E_C = \int_0^{V_R} C(V)VdV$$

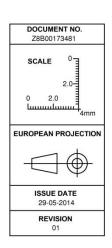


PG-TO252-2



*) mold flash not included

DIM	MILLIN	IETERS	INC	IES
DIM	MIN	MAX	MIN	MAX
Α	2.20	2.35	0.087	0.093
A1	0.00	0.15	0.000	0.006
b	0.65	0.85	0.026	0.033
b1	4	1.15		0.045
b2	1.05	1.45	0.041	0.057
b3	5.30	5.50	0.209	0.217
b4	1.	02	0.040	
С	0.46	0.58	0.018	0.023
c2	0.46	0.58	0.018	0.023
D	6.02	6.22	0.237	0.245
D1	5.04	5.44	0.198	0.214
E	6.45	6.65	0.254	0.262
E1	5.00		0.197	
е	4.57 (BSC)		0.180 (BSC)	
N	N 2		2	2
Н	9.40	10.40	0.370	0.409
L	1.19	1.39	0.047	0.055
D3	0.	20	0.0	800
L3	0.90	1.10	0.035	0.043





Revision History

IDM05G120C5

Revision: 2021-06-09, Rev. 2.1

Previous Revision:

Tevious revision.						
Revision Date Subjects (major changes since last version)		Subjects (major changes since last version)				
2.0	2015-08-28	Final data sheet				
2.1	2021-06-09	Increased dv/dt ruggedness				

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